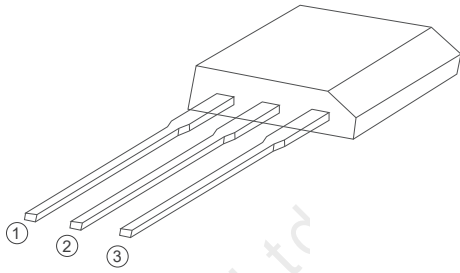


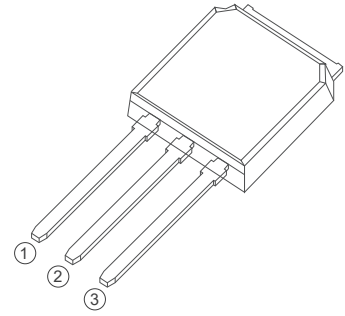
2P4M Series  
4A SCRs  
Sensitive Gate SCRs



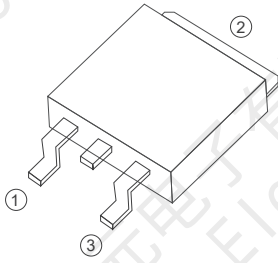
ShenZhenHanKingyuan  
Electronic CO.,Ltd



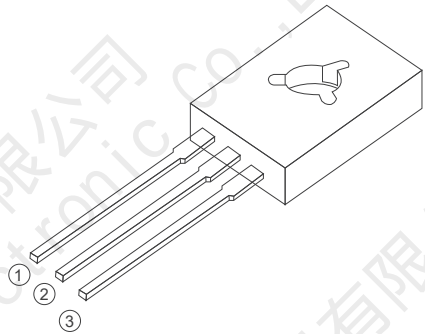
TO-202-3



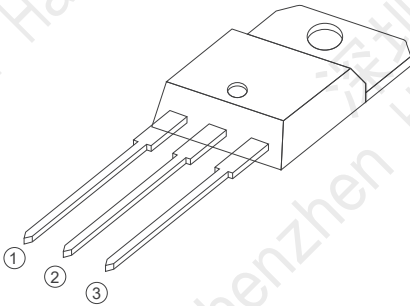
TO-251



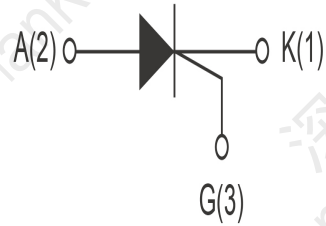
TO-252



TO-126



TO-220B Non-Insulated



### FEATURES

- > IT(RMS):4A
- > VGT: 0.8V
- > VDRM VRRM:600V

### APPLICATIONS

Washing machine,vacuums, massager,solid state relay, AC Motor speed regulation and so on.

**Absolute Maximum Ratings** (Tj=25°C unless otherwise specified)

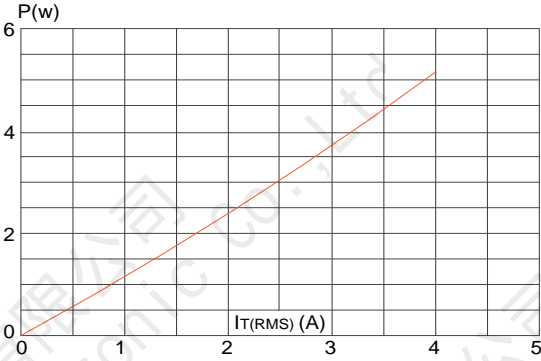
Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	X0405	600	V
IT(RMS)	R.M.S On-State Current		4	A
IT(AV)	average On-State Current		2.5	A
ITSM	Surge On-State Current	F=50Hz, tp=10ms	30	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Tp=10ms	4.5	A <sup>2</sup> s
IGM	Peak Gate Current	tp=20uS, Tj=110°C	1.2	A
PG(AV)	Average Gate Power Dissipation	Tj=110°C	0.2	W
PGM	Peak Gate Power Dissipation	tp=20uS, Tj=110°C	1	W
Tj	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

**Electrical Characteristics** (Tj=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value	Unit
IDRM	Repetitive Peak Off-State Current	Tc=25°C	≤5	uA
		Tc=110°C	≤100	uA
IRRM	Repetitive Peak Reverse Current	Tc=25°C	≤5	uA
		Tc=110°C	≤100	uA
VTM	Forward "on" voltage	IT=8A tp=380us	≤1.7	V
VGD	Gate nontrigger voltage	VD=VDRM, Tj=110°C, RGK=1KΩ, RL=3.3KΩ	≥0.2	V
IL	Latching current	IG=1.2IGT	≤6	mA
IH	Holding current	VD=12V, IGT=0.1A	≤5	mA
VGT	Gate trigger voltage	VD=12V	≤0.8	V
IGT	Gate trigger current	VD=12V, IT=0.1A	≤120	uA
dv/dt	Critical-rate of rise of commutation voltage	VD=2/3VDRM, Tj=110°C, RGK=1KΩ	≥10	V/us

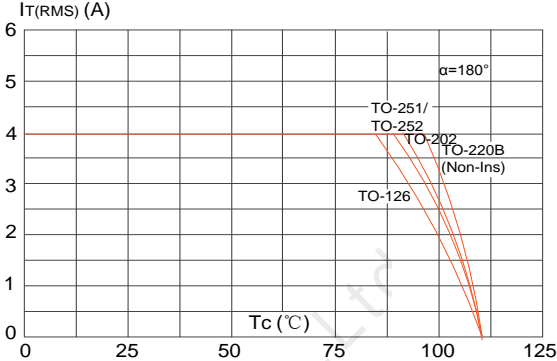
**FIG1**

Maximum power dissipation versus RMS on-state current



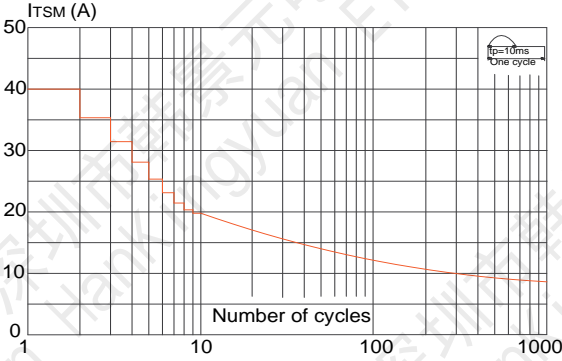
**FIG2**

RMS on-state current versus case temperature



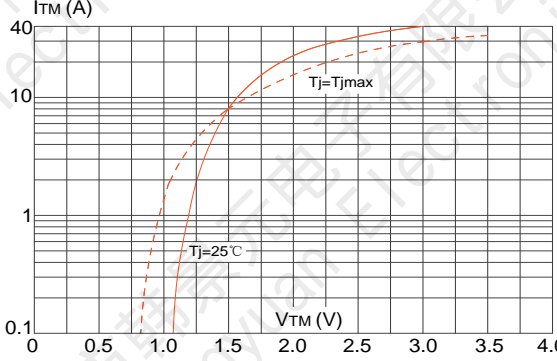
**FIG3**

Surge peak on-state current versus number of cycles



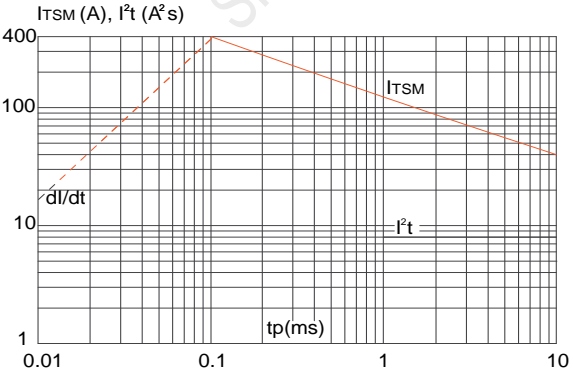
**FIG4**

On-state characteristics (maximum values)



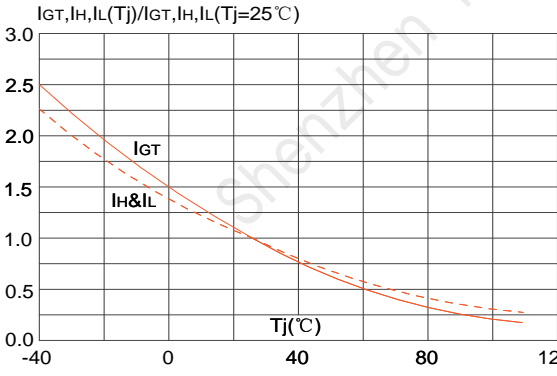
**FIG5**

Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\mu s$ , and corresponding value of  $I^2t$  ( $di/dt < 100A/\mu s$ )

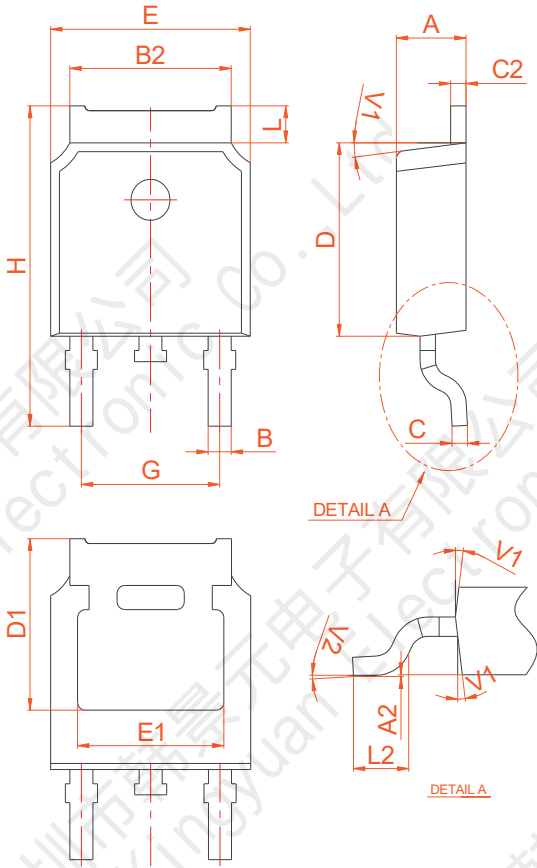


**FIG6**

Relative variations of gate trigger current, holding current and latching current versus junction temperature



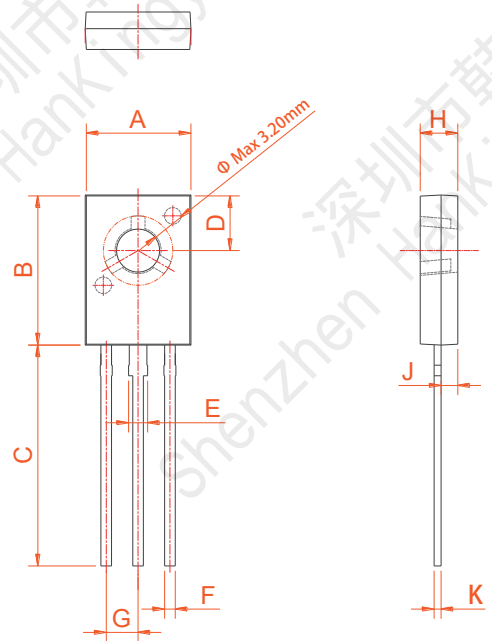
**PACKAGE MECHANICAL DATA**



TO-252

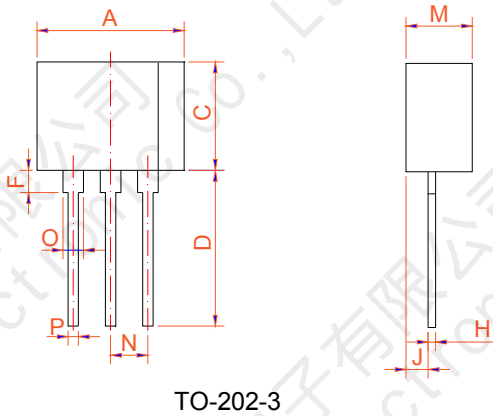
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.55	0.018		0.022
C2	2.70		2.90	0.106		0.114
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
L3		0.8			0.031	
L4		0.8			0.031	
V1		4°			4°	
V2	0°		8°	0°		8°

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024



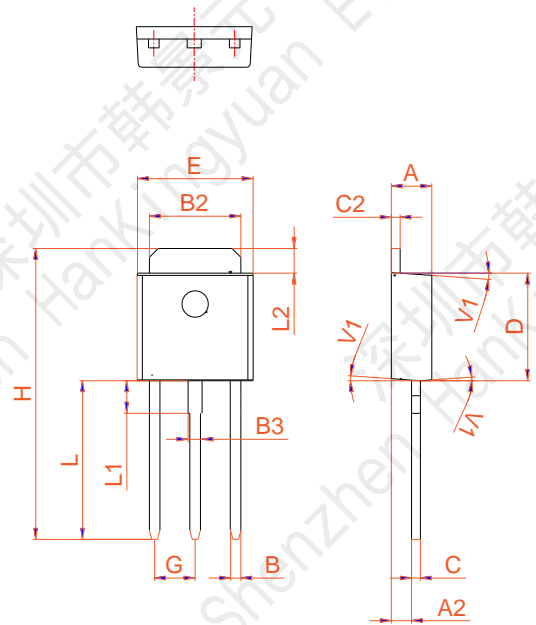
TO-126

**PACKAGE MECHANICAL DATA**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.30		9.90	0.366		0.390
C	7.0		7.6	0.276		0.299
D	10.5		11.5	0.413		0.453
F	1.50		2.50	0.059		0.098
H	0.45		0.55	0.018		0.022
J	1.50		1.90	0.059		0.075
M	4.40		4.70	0.173		0.185
N		2.54			0.100	
O	1.20		1.50	0.047		0.059
P	0.60		0.80	0.024		0.031

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	





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